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International Journal For Research in  
Applied Science and Engineering Technology



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# INTERNATIONAL JOURNAL FOR RESEARCH

IN APPLIED SCIENCE & ENGINEERING TECHNOLOGY

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**Volume: 2**

**Issue: V**

**Month of publication: May 2014**

**DOI:**

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# Fabrication of WS<sub>2</sub> Nanostructures Using Vapor Phase Deposition Method

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**Abstract:** *Direct growth of atomically thin WS<sub>2</sub> nanoplates and nanofilms on the SiO<sub>2</sub>/Si (300 nm) substrate by vapor phase deposition method without any catalyst is presented here. The WS<sub>2</sub> nanostructures were systematically characterized by optical microscopy, scanning electron microscopy, Raman microscopy and atomic force microscopy. It is found that growth time and growth temperature play important roles in the morphology of WS<sub>2</sub> nanostructures. Moreover, by using Kelvin probe force microscopy, it is understood that the WS<sub>2</sub> nanoplates exhibit uniform surface and charge distributions less than 10 mV fluctuations. The results may apply to the study of other transition metal dichalcogenides by vapor phase deposition method.*

**Key Words:** *Nanostructures, Thin film growth, Atomic force microscopy, Scanning electron Microscopy, Chemical exfoliation, Optoelectronics.*

## 1. INTRODUCTION

The emergence of graphene has drawn much attention due to its unique properties and potential applications [1-2]. Nevertheless, the absence of graphene band gap hinders its usefulness in field effect transistors because of the low current on/off ratio. Therefore, many other layered materials, such as boron nitride, and topological insulators, have been prepared and extensively studied [3]. Recently, layered transition metal dichalcogenides (MX<sub>2</sub> (M=Mo, W; X=S, Se) have attracted a great deal of attention for their wide applications in the field of optoelectronics [4-6], catalysis [7-10], energy [11-12] harvesting [8], and nano-electromechanical systems [13].

The WS<sub>2</sub> has a layered structure of S-W-S stacking layers made up from a basic unit cell, which is held together by van der Waals forces shown in fig 1(a). Recent investigations have demonstrated that WS<sub>2</sub>-based devices have high performance with low power consumption at room temperature. The transition from indirect-to-direct band gap occurs when the dimension is reduced from bulk to monolayer, which shows promising applications in valleytronics and valley-based optoelectronics [14-15]. Therefore, the controllable nanostructure synthesis of these materials becomes essential. In this work, the studies are mainly focused on the synthesis and characterization of WS<sub>2</sub> nanostructures [16].

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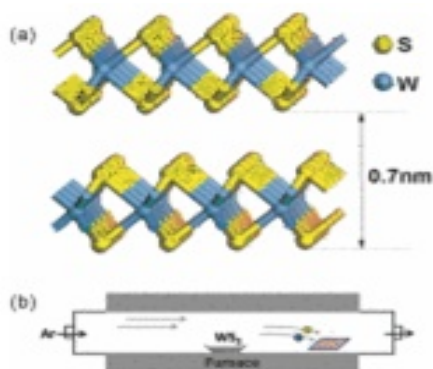


Figure 1. (a) Lattice structure of layered WS<sub>2</sub>. (b) Schematic of CVD process for the growth of WS<sub>2</sub> nanostructures.

Currently, various methods have been employed to fabricate WS<sub>2</sub>, including micromechanical cleavage technique [16], chemical exfoliation [17] and hydrothermal synthesis [18]. However, the thickness and size of the flakes are not controllable by these methods, which are infeasible for the integration of corresponding devices [19-21]. High quality WS<sub>2</sub> nanostructure synthesis remains challenging. Chemical vapor deposition (CVD) is the most expected method to synthesize single-layer, uniform and large scale WS<sub>2</sub> films. However, previous reports indicate that large areas of WS<sub>2</sub> thin films are mainly obtained by using WO<sub>3</sub>, HS<sub>2</sub> or sulfur as the reactants [22-23].

A simple vapor phase deposition method for the growth of WS<sub>2</sub> nanostructures by decomposing WS<sub>2</sub> powder at high temperature is described here. WS<sub>2</sub> nanoplates as well as a large area of thin films were directly synthesized on

SiO<sub>2</sub> substrate, and were systematically characterized. The electrostatic properties of WS<sub>2</sub> nanostructures were investigated by Kelvin probe force microscopy, which has been widely applied to other layered materials such as graphene, MoS<sub>2</sub> and topological insulators [24]. The uniform surface and charge distributions provide insight into the electronic properties of these WS<sub>2</sub> nanostructure-based devices [25-27].

## 2. EXPERIMENTAL DETAILS

### 2.1. Synthesis of WS<sub>2</sub> nanostructures

WS<sub>2</sub> nanostructures were synthesized on the SiO<sub>2</sub>/Si substrate in a horizontal tube furnace (Lindberg/Blue M) by vapor phase deposition method without any catalyst as shown in the reaction setup shown in fig 1(b). WS<sub>2</sub> powders (99.9%) were placed in the hot center of the furnace. The SiO<sub>2</sub>/Si substrates cleaned with standard piranha solution were localized at the downstream zones 14 cm away (14-16 cm) from the hot center. The source material was heated to growth temperature (950–1000 °C) at a rate of 25 °C/min and maintained for an hour or half an hour before cooling down to room temperature naturally. During the procedure of the synthesis, the growth pressure was kept at 110 Pa within the 150 sccm Ar-H<sub>2</sub> gas flow (5% H<sub>2</sub>).

### 2.2. Characterization

The morphologies of WS<sub>2</sub> nanostructures were characterized by scanning electron microscopy (SEM, JEOL,

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JSM-6360) equipped with an energy dispersive X-ray spectrometer (EDX). Raman spectra were collected at room temperature in Renishaw micro-Raman spectrometer with 532 nm laser excitation light. The atomic force microscopy (AFM, SEIKO, SPI3800N + 300 HV) images were characterized to determine the thickness of WS<sub>2</sub> nanostructures. The electrostatic properties were investigated by Kelvin probe force microscopy (AFM, SEIKO, SPI3800N + 300 HV) under ambient conditions.

### 3. RESULT AND DISCUSSION

Fig 2(a) exhibits a SEM image of WS<sub>2</sub> samples, which were synthesized at 1000 °C and maintained for 30 mins. It can be clearly seen that triangular WS<sub>2</sub> nanoplates were fabricated on the SiO<sub>2</sub>/Si substrate with lateral dimension up to several micrometers. And the elemental compositions of synthesized WS<sub>2</sub> nanoplates were determined by EDX analysis is given in fig 2(b). The atomic contents of S and W are 66.6%, 33.4%, respectively, which are in good agreement with the WS<sub>2</sub> formula and suggests successful fabrication of WS<sub>2</sub> nanoplates.

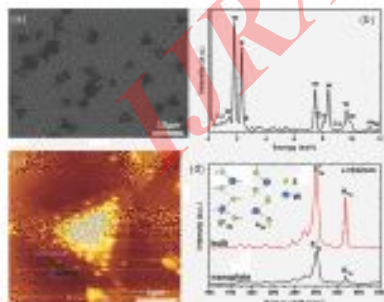


Figure 2(a) SEM image of triangular WS<sub>2</sub> nanoplates grown on SiO<sub>2</sub>/Si substrate. (b) EDX spectrum of synthesized WS<sub>2</sub> nanoplates. (c) AFM image of single WS<sub>2</sub> nanoplate. (d) Raman spectra of few-layer WS<sub>2</sub> nanoplates and bulk WS<sub>2</sub>.

Fig 2(c) is the AFM image of a single triangular WS<sub>2</sub> nanoplate. The thickness is ~ 2.6 nm corresponding to 4 layers of WS<sub>2</sub>, which indicates the successful synthesis of ultrathin nanoplates via vapor-solid mechanism. During the growth process, the WS<sub>2</sub> powders were heated under high temperature and decomposed to W and S atoms, which recombined at the low temperature zone. At the initial growth stage, nucleation formed randomly on the SiO<sub>2</sub>/Si substrate. With the formation of the nucleation centers, the incoming W and S atoms tended to bond covalently with the edge of nucleation due to the dangling bonds existence. Therefore, the growth rate of lateral dimension is fast compared to the c-axis, resulting in the formation of nanoplate structure.

Raman spectroscopy was further performed to investigate the crystal structure and quality of few-layer WS<sub>2</sub> nanoplates. For the crystal structure of WS<sub>2</sub>, there are 18 lattice dynamical modes: two dominant modes of E<sub>2g</sub> and A<sub>1g</sub> are investigated in the present work. The A<sub>1g</sub> mode reflects the out-of-plane displacement of S atoms and the E<sub>2g</sub> mode involves the in-plane displacement of W and S atoms. As shown in fig 2(d), the E<sub>2g</sub> and A<sub>1g</sub> modes of few-layer WS<sub>2</sub> nanoplates have appeared at 349.7 cm<sup>-1</sup> and 416.7 cm<sup>-1</sup>, respectively. In contrast, the two modes of the WS<sub>2</sub> bulk are located at 350.3 cm<sup>-1</sup> (E<sub>2g</sub>) and 418.9 cm<sup>-1</sup> (A<sub>1g</sub>). A<sub>1g</sub> mode



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exhibits a blue-shift with the increase of the thickness due to the increasing van der Waals forces among layers, which is in good agreement with previous reports [23]. Raman results indicate high quality of synthesized  $WS_2$  nanoplates.

To investigate the growth process of  $WS_2$  nanostructures, the influences of growth time and temperature have been systematically conducted. When the growth time is prolonged to 60 mins under the experimental conditions mentioned above, it is seen that amounts of  $WS_2$  nanoplates have been obtained and randomly distributed on the  $SiO_2/Si$  substrate. Fig 3(a) is the optical image: it clearly shows that some nanoplates merged together. The corresponding SEM image is shown in fig 3(b). Large areas of  $WS_2$  nanofilms with several hundred micrometers were simultaneously fabricated as shown in the optical and SEM images fig 3 (c-d), which deposited on the same substrate with different distance compared with (a-b). By comparison, it can be concluded that the temperature is one of the factors, which influence the thickness and size of the  $WS_2$  nanoplates.  $W$  nanowires with tens of micrometers were also obtained, which have been demonstrated by EDX analysis, further confirming the decomposition of  $WS_2$  during the heating process.

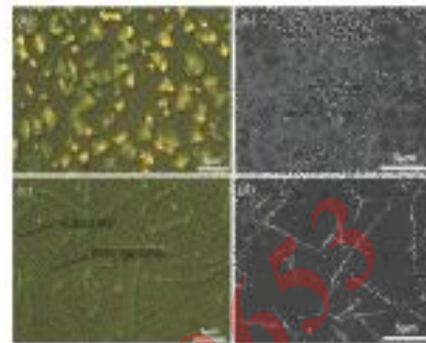


Figure 3(a) Photograph of few-layer  $WS_2$  nanoplates on the  $SiO_2/Si$  substrate. (b) Corresponding SEM image. (c-d) Optical and SEM images of large area  $WS_2$  films.

It is interesting that, when the growth temperature in the hot center was reduced to  $950^\circ C$  and the growth time has been maintained for 60 mins, the  $WS_2$  nanoplates with random shape were synthesized (16–18 cm away from the hot center). Fig 4(a) shows the corresponding SEM image. Under such growth conditions, large areas of thin films were first grown on the whole substrate. Then the growth continues on the thin film, forming  $WS_2$  nanostructures with random shapes. Fig 4(b) is a typical AFM image with the 0.5 nm surface roughness of the irregular  $WS_2$  nanostructure. However, the surface roughness of the thin films is larger with 3 nm. Although the growth mechanism is not clear, the large areas of  $WS_2$  nanostructure will benefit from the integration of  $WS_2$ -based devices.

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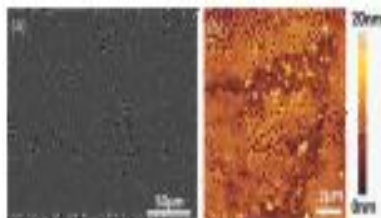


Figure 4(a) SEM image of irregular WS<sub>2</sub> nanofilms fabricated under 950 °C growth temperature. (b) Corresponding AFM image of WS<sub>2</sub> nanofilms.

WS<sub>2</sub> nanostructures present many promising applications in nanoelectronics and optoelectronics, [19–28], which have been extensively investigated. Nevertheless, there are few reported studies on the electrostatic properties of WS<sub>2</sub> and the interface between the WS<sub>2</sub> nanostructure and electrode, which are actually essential for the performance of WS<sub>2</sub>-based devices. Herein, the electrostatic properties of the WS<sub>2</sub> nanostructures under ambient environment by employing Kelvin probe force microscopy were also studied. Fig 5(a) is the typical AFM image of the WS<sub>2</sub> nanostructures. Fig 5(b) is the corresponding surface potential image. The surface potential value of the WS<sub>2</sub> nanostructure is around 650 mV with 10 mV fluctuations across the whole area. The observation of the relatively homogeneous surface potential and charge distributions were observed, which also confirmed the high quality of the synthesized samples

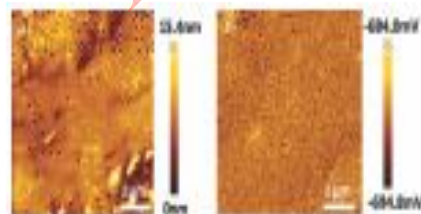


Figure 5 (a) A typical AFM image of WS<sub>2</sub> nanofilm. (b) Corresponding surface potential image.

### Conclusion

Fabrication of the WS<sub>2</sub> nanostructures on the SiO<sub>2</sub>/Si substrate via vapor phase deposition method without any catalyst is done this manner. The influence of growth time and temperature on the WS<sub>2</sub> nanostructures was investigated. The results demonstrate that the temperature is one of the important factors, which influence the thickness and size of the WS<sub>2</sub> nanoplates. While, the growth time mainly affect the quantity of the samples.

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